

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-4. (Canceled).

5. (Currently Amended) A method for evaluating crystal defects of a silicon wafer comprising:

evaluating crystal defects of a silicon wafer by etching a surface of the silicon wafer by immersing the wafer in an etching solution; solution and

observing etch pits formed on the etched surface of the wafer,

wherein the silicon wafer of which crystal defects are evaluated has low electrical resistivity of $1 \Omega \cdot \text{cm}$ or less, and the etching solution is a mixture of hydrofluoric acid, nitric acid, acetic acid and water further including iodine or iodide, the etching solution ~~satisfies at least one of (i) having~~ a volume ratio of hydrofluoric acid : nitric acid : acetic acid : ~~water is~~ water of 1 : 13-17 : 4-8 : 4-8 ~~and/or (ii) and~~ includes iodine or iodide in a range from 0.01 g to 0.09 g per 1 liter of total liquid volume of the etching solution to decrease the etching rate of the etching solution, and the etching solution is adjusted to have an etching rate of 100 nm/min or less for the silicon wafer.

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Previously Presented) The method for evaluating crystal defects of a silicon wafer according to Claim 5, wherein a removal amount of the surface of the silicon wafer by etching is 50 nm or more.

10-12. (Canceled)